

# MANUFACTURE OF SEMICONDUCTOR DEVICE, MANUFACTURE OF ELECTRO-OPTICAL DEVICE, SEMICONDUCTOR DEVICE AND THE ELECTRO-OPTICAL DEVICE

**Patent number:** JP2000312006

**Publication date:** 2000-11-07

**Inventor:** MURAIDE MASAO

**Applicant:** SEIKO EPSON CORP

**Classification:**


**- international:** H01L29/786; H01L21/336; G02F1/1368; H01L27/108; H01L21/8242

**- european:**

**Application number:** JP20000027112 20000204

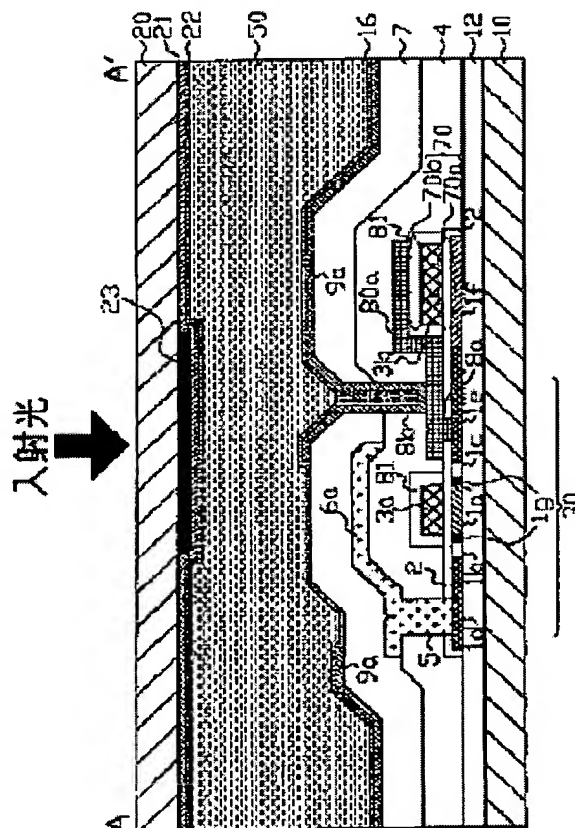
**Priority number(s):** JP19990050673 19990226; JP20000027112 20000204

**Also published as:**

 US 6569717 (B1)

## Abstract of JP2000312006

**PROBLEM TO BE SOLVED:** To provide a highly reliable semiconductor device or an electro-optical device having a thin-film transistor, and having no alignment deviation, even when the thin film transistor is brought into a microscopic state. **SOLUTION:** A liquid crystal device, which is an example of an electro-optical device, is provided with a TFT 30 formed on a TFT array substrate 10, a data line 6a, a scanning line 3a, the second capacitor electrode 3b and a pixel electrode 9a. The pixel electrode and the TFT are electrically connected by two contact holes 8a and 8b relayed by a conductive layer 80a. A second insulating thin film 81 is pinched by the second capacity electrode and a part of the conductive layer, and the second accumulation capacitor is formed. The second insulating thin film is composed of the scanning line and the oxide film of the second capacitor electrode.



Data supplied from the esp@cenet database - Worldwide